

# LINEAR SYSTEMS

Twenty-Five Years Of Quality Through Innovation

## IT120A IT120 IT121 IT122

### MONOLITHIC DUAL NPN TRANSISTORS

#### FEATURES

Direct Replacement for Intersil IT120 Series  
Pin for Pin Compatible

#### ABSOLUTE MAXIMUM RATINGS NOTE 1 ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

$I_C$  Collector-Current 10mA

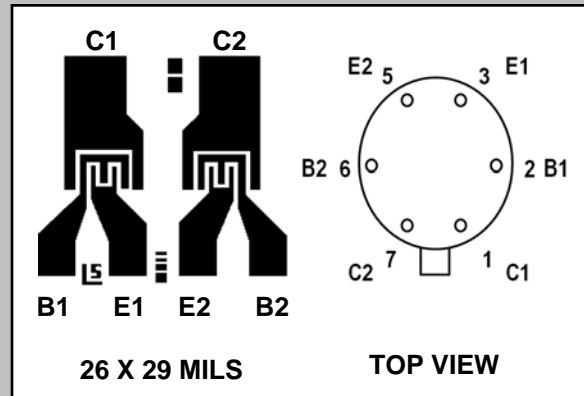
#### Maximum Temperatures

Storage Temperature Range  $-65^\circ\text{C}$  to  $+150^\circ\text{C}$

Operating Temperature Range  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$

#### Maximum Power Dissipation

	ONE SIDE	BOTH SIDES
Device Dissipation $T_A = 25^\circ\text{C}$	250mW	500mW
Linear Derating Factor	2.3mW/ $^\circ\text{C}$	4.3W/ $^\circ\text{C}$

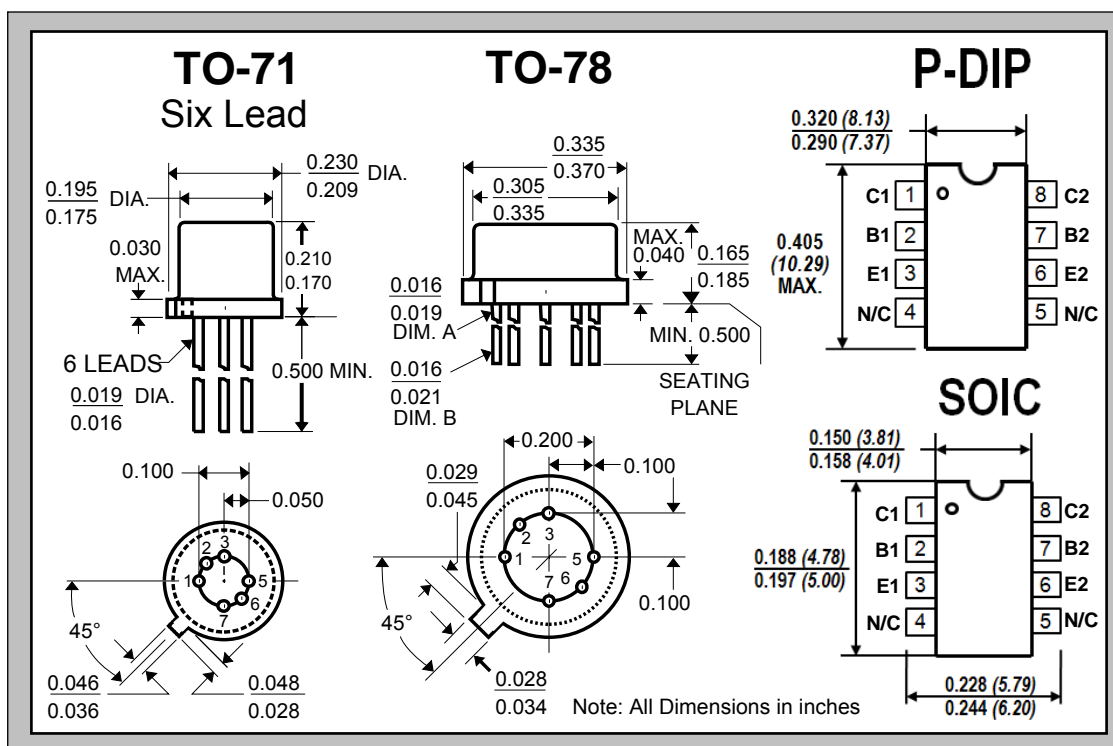


#### ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ (unless otherwise noted)

SYMBOL	CHARACTERISTIC	IT120A	IT120	IT121	IT122		UNITS	CONDITIONS
$BV_{CBO}$	Collector to Base Voltage	45	45	45	45	MIN.	V	$I_C = 10\mu\text{A}$ $I_E = 0\text{A}$
$BV_{CEO}$	Collector to Emitter Voltage	45	45	45	45	MIN.	V	$I_C = 10\mu\text{A}$ $I_B = 0\text{A}$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	6.2	6.2	6.2	6.2	MIN.	V	$I_E = 10\mu\text{A}$ $I_C = 0\text{A}$ <b>NOTE 2</b>
$BV_{CCO}$	Collector to Collector Voltage	60	60	60	60	MIN.	V	$I_{CCO} = 10\mu\text{A}$ $I_B = I_E = 0\text{A}$
$h_{FE}$	DC Current Gain	200	200	80	80	MIN.		$I_C = 10\mu\text{A}$ $V_{CE} = 5\text{V}$
		225	225	100	100	MIN.		$I_C = 1.0\text{mA}$ $V_{CE} = 5\text{V}$
$V_{CE(SAT)}$	Collector Saturation Voltage	0.5	0.5	0.5	0.5	MAX.	V	$I_C = 0.5\text{mA}$ $I_B = 0.05\text{mA}$
$I_{EBO}$	Emitter Cutoff Current	1	1	1	1	MAX.	nA	$I_C = 0$ $V_{EB} = 3\text{V}$
$I_{CBO}$	Collector Cutoff Current	1	1	1	1	MAX.	nA	$I_E = 0$ $V_{CB} = 45\text{V}$
$C_{OBO}$	Output Capacitance <sup>3</sup>	2	2	2	2	MAX.	pF	$I_E = 0$ $V_{CB} = 5\text{V}$
$C_{C1C2}$	Collector to Collector Capacitance <sup>3</sup>	2	2	2	2	MAX.	pF	$V_{CC} = 0$
$I_{C1C2}$	Collector to Collector Leakage Current	$\pm 500$	$\pm 500$	$\pm 500$	$\pm 500$	MAX.	nA	$V_{CCO} = \pm 60\text{V}$ $I_B = I_E = 0\text{A}$
$f_T$	Current Gain Bandwidth Product <sup>3</sup>	220	220	180	180	MIN.	MHz	$I_C = 1\text{mA}$ $V_{CE} = 5\text{V}$
NF	Narrow Band Noise Figure <sup>3</sup>	3	3	3	3	MAX.	dB	$I_C = 100\mu\text{A}$ $V_{CE} = 5\text{V}$ $BW = 200\text{Hz}$ , $R_G = 10\text{K}\Omega$ $f = 1\text{KHz}$

**MATCHING CHARACTERISTICS @ 25°C (unless otherwise noted)**

SYMBOL	CHARACTERISTIC	IT120A	IT120	IT121	IT122		UNITS	CONDITIONS
$ V_{BE1}-V_{BE2} $	Base Emitter Voltage Differential	1	2	3	5	MAX.	mV	$I_C = 10 \mu A$ $V_{CE} = 5V$
$\Delta  V_{BE1}-V_{BE2}  / \Delta T$	Base Emitter Voltage Differential Change with Temperature <sup>3</sup>	3	5	10	20	MAX.	$\mu V/^\circ C$	$I_C = 10 \mu A$ $V_{CE} = 5V$ $T = -55^\circ C$ to $+125^\circ C$
$ I_{B1}-I_{B2} $	Base Current Differential	2.5	5	25	25	MAX.	nA	$I_C = 10 \mu A$ $V_{CE} = 5V$



**NOTES:**

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired.
2. The reverse base-to-emitter voltage must never exceed 6.2 volts; the reverse base-to-emitter current must never exceed 10  $\mu A$ .
3. Not a production test.

Linear Integrated Systems (LIS) is a 25-year-old, third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company President John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, co-founder and vice president of R&D at Intersil, and founder/president of Micro Power Systems.